

S4D20120A S4D20120H S4D20120G 1200V SIC POWER SCHOTTKY RECTIFIERS

Description

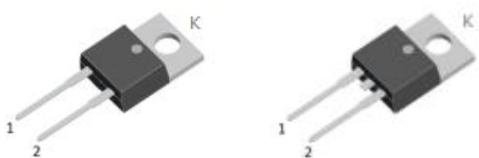
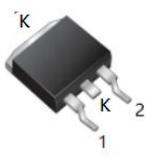
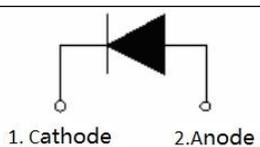
This 1200V 20A diode is high voltage Schottky rectifier that has very low total conduction losses and very stable switching characteristics over temperature extremes. The S4D20120A/S4D20120H/S4D20120G are ideal for energy sensitive, high frequency applications in challenging environments.

Features

- 175°C T_J operation
- Ultra-low switching loss
- Switching speeds independent of operating temperature
- Low total conduction losses
- High forward surge current capability
- High package isolation voltage
- Terminals finish: 100% Pure Tin
- “-A” is an AEC-Q101 qualified device
- Pb – Free Device
- All SMC parts are traceable to the wafer lot
- Additional electrical and life testing can be performed upon request

Applications

- Alternative energy inverters
- Power Factor Correction (PFC)
- Free-Wheeling diodes
- Switching supply output rectification
- Reverse polarity protection

<p>S4D20120A</p> 	<p>S4D20120G</p> 	<p>S4D20120H</p> 
<p>TO-220AC (TO-220-2)</p>	<p>D²PAK (TO-263-2)</p>	<p>TO-247AC (TO-247-2)</p>
		 <p>1. Cathode 2. Anode</p>

Maximum Ratings

Characteristics	Symbol	Condition	Max.	Units
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V_{RRM} V_{RWM} V_R	-	1200	V
Average Rectified Forward Current	$I_{F(AV)1}$	@Tc=25°C	57	A
	$I_{F(AV)2}$	@Tc=150°C	20	A
Repetitive Peak Forward Surge Current	I_{FRM1}	10 ms, Half Sine pulse, Tc =25°C	86	A
	I_{FRM2}	10 ms, Half Sine pulse, Tc =110°C	56	A
Peak One Cycle Non-Repetitive Surge Current	I_{FSM1}	10ms, Half Sine pulse, Tc =25°C	248	A
	I_{FSM2}	10ms, Half Sine pulse, Tc =110°C	205	A
Non-Repetitive Peak Forward Surge Current	$I_{F,Max1}$	10µs. Pulse, Tc =25°C	1150	A
	$I_{F,Max2}$	10µs. Pulse, Tc =110°C	950	A
Power Dissipation	P_{tot1}	Tc =25°C	245.9	W
	P_{tot2}	Tc =110°C	106.6	W

Electrical Characteristics:

Characteristics	Symbol	Condition	Typ.	Max.	Units
Forward Voltage Drop*	V_{F1}	@ 20A, Pulse, T _J = 25 °C	1.5	1.8	V
	V_{F2}	@ 20A, Pulse, T _J = 175 °C	2.2	3.0	V
Reverse Current*	I_{R1}	@V _R = rated V _R T _J = 25 °C	1	25	µA
	I_{R2}	@V _R = rated V _R T _J = 175 °C	10	150	µA
Junction Capacitance	C_T	V _R =0V, T _J =25°C, f=1MHz	1620	-	pF
Reverse Recovery Charge	Q_c	I _F = 20A, di/dt = 200A/µs V _R = 800 V, T _J =25°C	124.89	-	nC
Capacitance Stored Energy	E_C	V _R = 800 V, T _J =25°C	64.20	-	µJ

* Pulse width < 300 µs, duty cycle < 2%

Thermal-Mechanical Specifications:

Characteristics	Symbol	S4D20120A	S4D20120H	S4D20120G	Units
Junction Temperature	T _J	-55 to +175			°C
Storage Temperature	T _{stg}	-55 to +175			°C
Typical Thermal Resistance Junction to Case	R _{θJC}	0.6	0.61	0.6	°C/W

Ordering Information

Device	Package	Shipping
S4D20120A	TO-220AC(TO-220-2)	50pcs / tube
S4D20120H	TO-247AC(TO-247-2)	25pcs / tube
S4D20120G	D2PAK(TO-263-2)	800pcs/reel
S4D20120GTR	D2PAK(TO-263-2)	800pcs/reel

For information on tape and reel specifications, including part orientation and tape sizes, please refer to our tape and reel packaging specification.

Ratings and Characteristics Curves

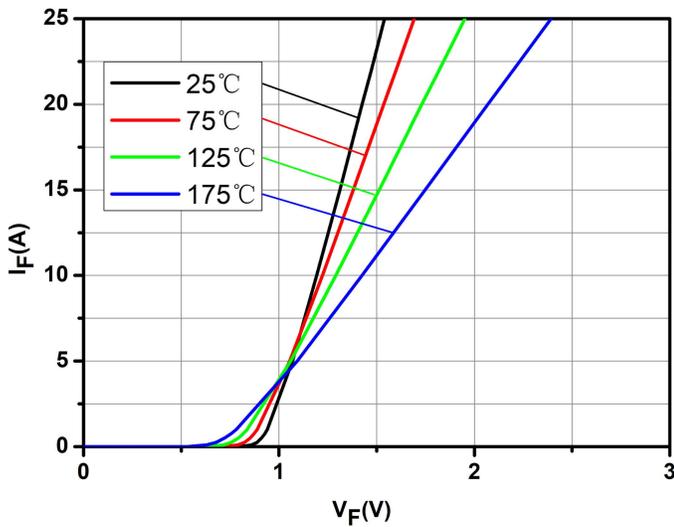


Fig.1-Typical Forward Voltage Characteristics

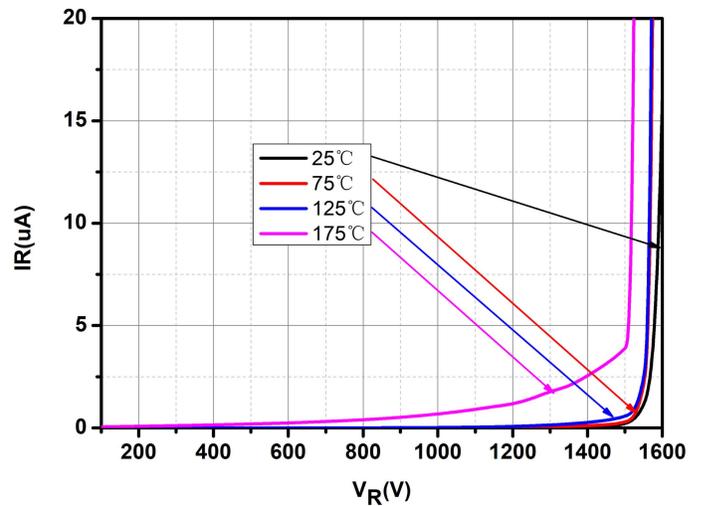


Fig.2-Typical Reverse Characteristics

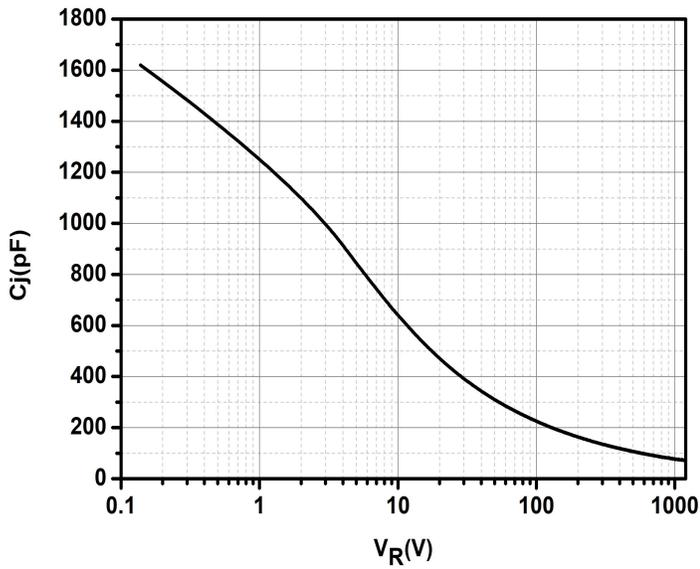


Fig.3-Capacitance vs. Reverse Voltage

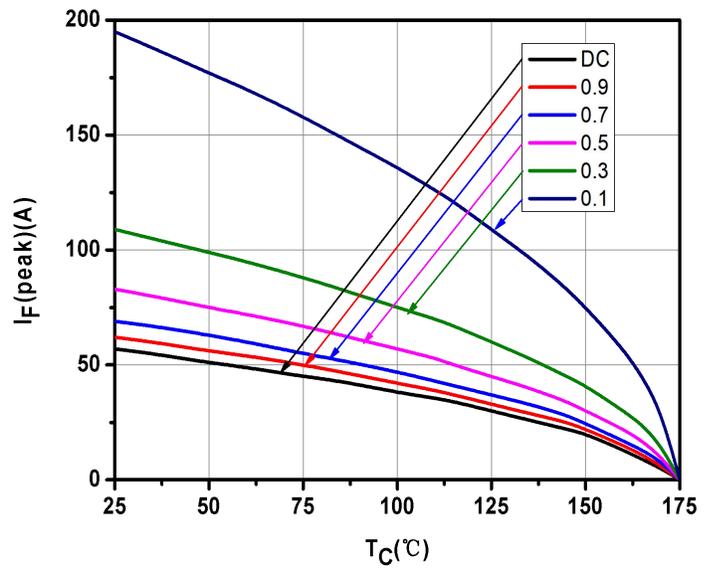


Fig.4-Current Derating

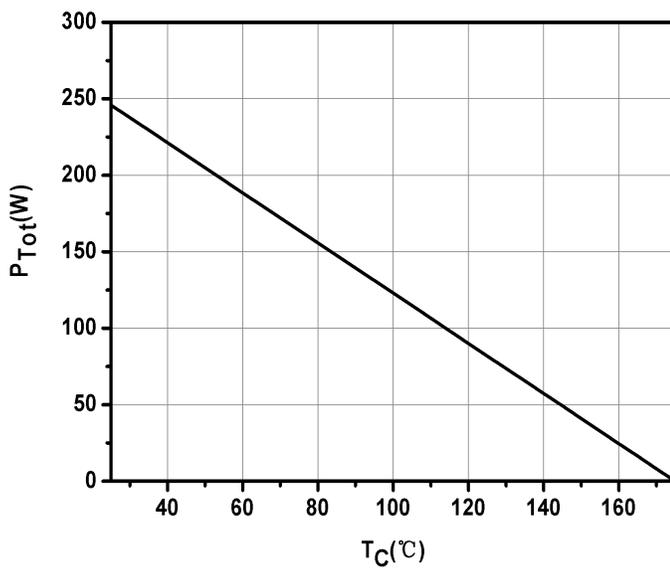


Fig.5-Power Derating

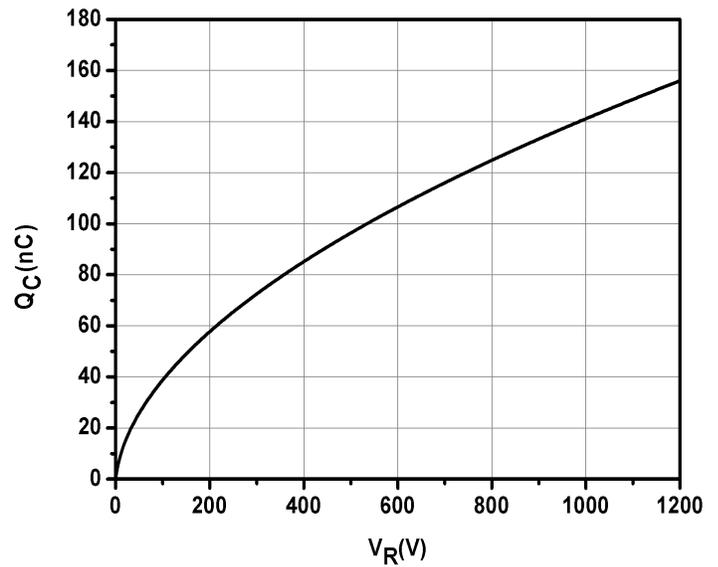


Fig.6-Total Capacitance Charge vs. Reverse Voltage

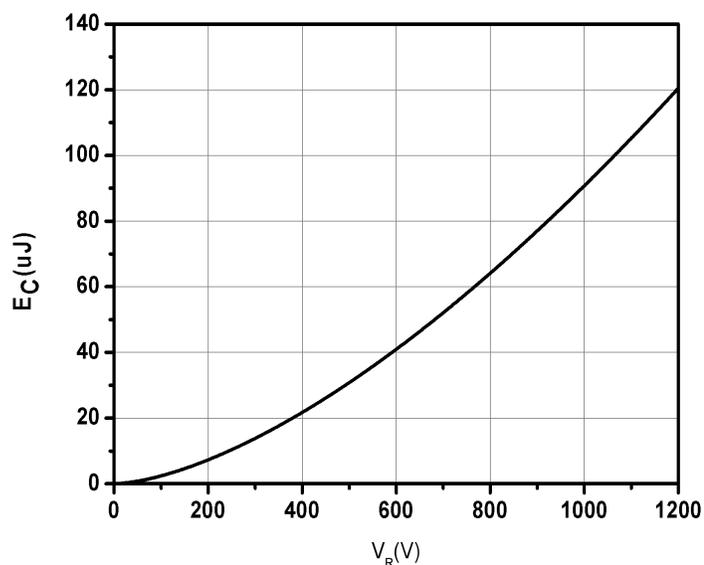


Fig.7-Capacitance Stored Energy

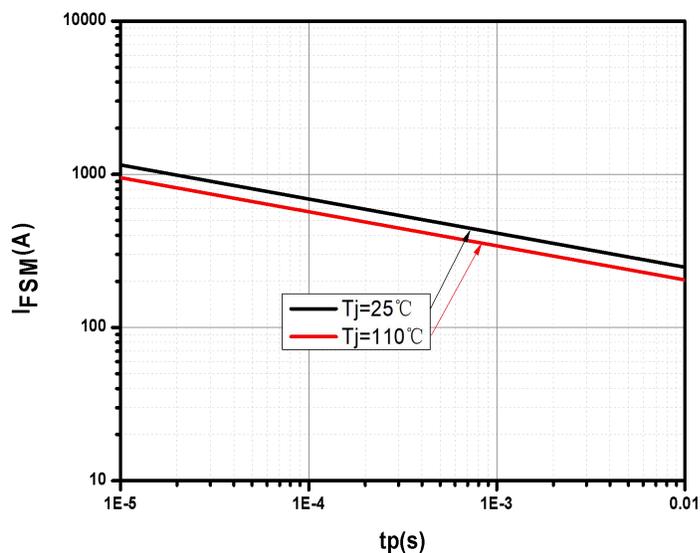
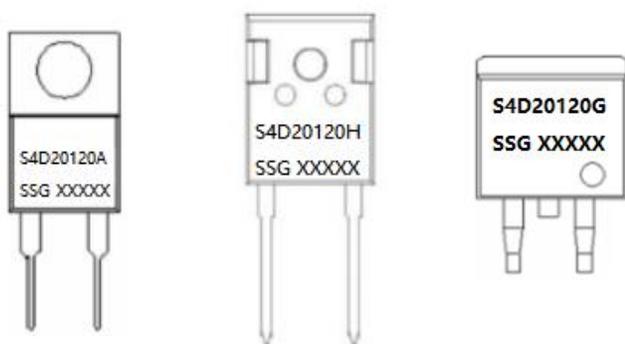


Fig.8-Non-repetitive peak forward surge current versus pulse duration (sinusoidal waveform)

Marking Diagram

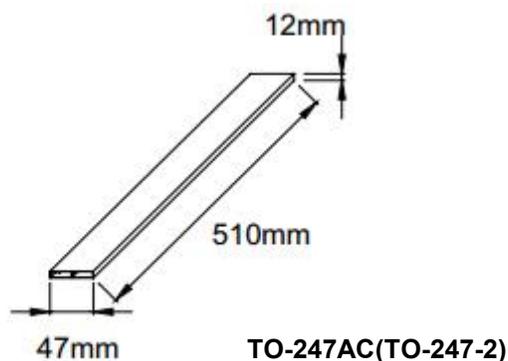
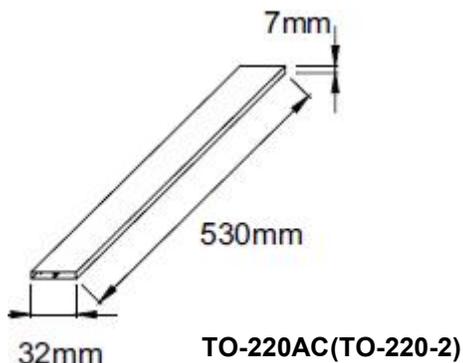


Where XXXXX is YYWWL

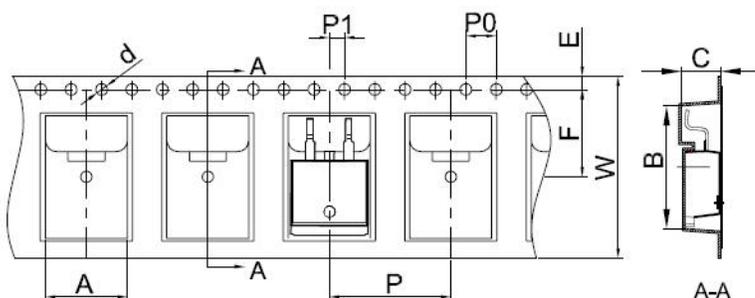
S4D = Device Type
A/H/G = Package type
20 = Forward Current (20A)
120 = Reverse Voltage (1200V)
SSG = SSG
YY = Year
WW = Week
L = Lot Number

Cautions: Molding resin
Epoxy resin UL:94V-0

Tube Specification

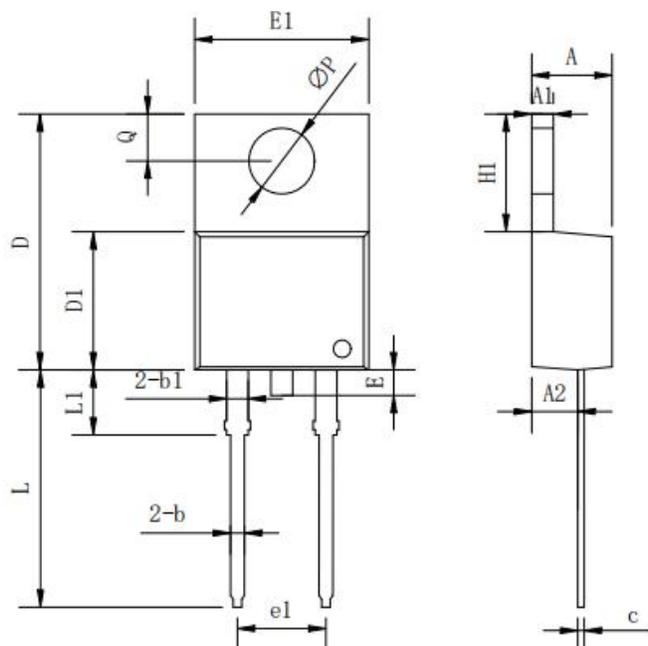


Carrier Tape & Reel Specification D2PAK(TO-263-2)



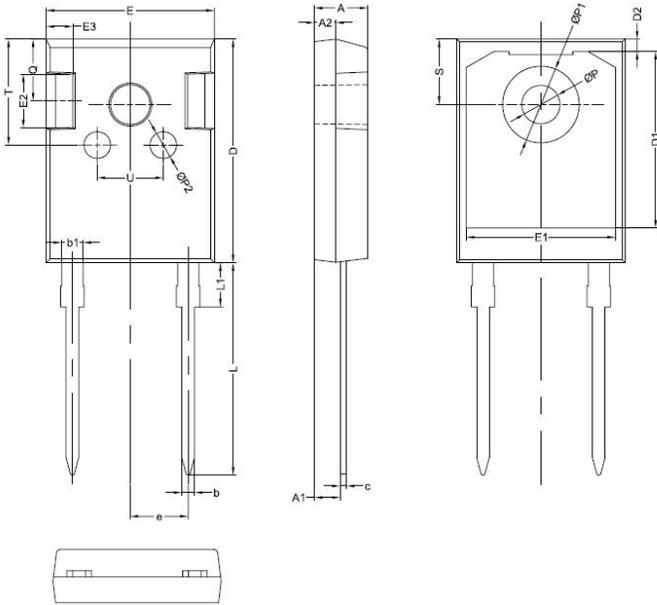
SYMBOL	Millimeters	
	Min.	Max.
A	10.70	10.90
B	16.03	16.23
C	5.11	5.31
d	1.45	1.65
E	1.65	1.85
F	11.40	11.60
P0	3.90	4.10
P	15.90	16.10
P1	1.90	2.10
W	23.90	24.30

Mechanical Dimensions TO-220AC(TO-220-2)



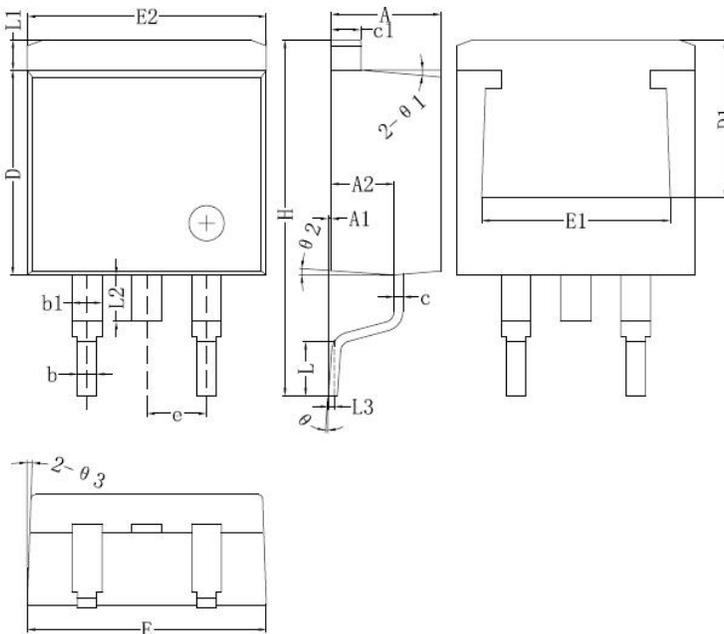
Symbol	Dimensions in millimeters		
	Min.	Typical	Max.
A	3.56	-	4.83
A1	0.51	-	1.40
A2	2.03	-	2.92
b	0.38	-	1.02
b1	1.14	-	1.78
c	0.31	-	0.61
D	14.22	-	16.51
D1	8.38	-	9.42
E	-	-	1.78
E1	9.65	10.16	10.67
e1	-	5.08	-
H1	5.84	-	6.86
L	12.70	-	14.73
L1	-	-	6.35
ΦP	-	3.56	-

Mechanical Dimensions TO-247AC(TO-247-2)



SYMBOL	Millimeters		
	MIN.	TYP.	MAX.
A	4.80	5.00	5.20
A1	2.20	2.41	2.61
A2	1.90	2.00	2.10
b	1.10	1.20	1.35
b1	1.80	2.00	2.20
c	0.50	0.60	0.75
D	20.30	21.00	21.20
D1		16.58	
D2		1.17	
E	15.60	15.80	16.00
E1		14.02	
E2		5.00	
E3		2.50	
e		5.44	
L	19.42	19.92	20.42
L1		4.13	
P	3.50	3.60	3.70
P1	7.1	7.19	7.40
P2		2.50	
Q		5.80	
S	6.05	6.15	6.25
T		10.00	
U		6.20	

Mechanical Dimensions D²PAK(TO-263-2)



Symbol	Dimensions in millimeters	
	Min.	Max.
A	4.06	4.83
A1	0	0.26
b	0.51	0.99
b1	1.14	1.78
c	0.31	0.74
c1	1.14	1.65
D	8.38	9.65
D1	6.4	
E1	6.22	
E2	9.65	10.67
e	2.54BSC	
H	14.6	15.88
L	1.78	2.8
L1	-	1.68
L2	-	2.2
L3	0.255BSC	
Θ	0	8°

Technical Data
Data Sheet N2367, REV.G



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